

BIPOLAR ANALOG INTEGRATED CIRCUIT UPC3226TB

5 V, SILICON GERMANIUM MMIC MEDIUM OUTPUT POWER AMPLIFIER

DESCRIPTION

The μ PC3226TB is a silicon germanium (SiGe) monolithic integrated circuit designed as IF amplifier for DBS tuners. This IC is manufactured using our 50 GHz f_{max} UHS2 (<u>U</u>Itra <u>High Speed Process</u>) SiGe bipolar process.

FEATURES

| Low current | : Icc = 15.5 mA TYP. @ Vcc = 5.0 V |
|---|---|
| Medium output power | : Po (sat) = +13.0 dBm TYP. @ f = 1.0 GHz |
| | : Po (sat) = +9.0 dBm TYP. @ f = 2.2 GHz |
| High linearity | : Po (1dB) = +7.5 dBm TYP. @ f = 1.0 GHz |
| | : Po (1dB) = +5.7 dBm TYP. @ f = 2.2 GHz |
| Power gain | : G _P = 25.0 dB TYP. @ f = 1.0 GHz |
| | : G _P = 26.0 dB TYP. @ f = 2.2 GHz |
| Noise Figure | : NF = 5.3 dB TYP. @ f = 1.0 GHz |
| | : NF = 4.9 dB TYP. @ f = 2.2 GHz |
| Supply voltage | : Vcc = 4.5 to 5.5 V |
| Port impedance | : input/output 50 Ω |

APPLICATIONS

• IF amplifiers in LNB for DBS converters etc.

ORDERING INFORMATION

| Part Number | Order Number | Package | Marking | Supplying Form |
|--------------|----------------|---|---------|---|
| μΡC3226TB-E3 | μΡC3226TB-E3-A | 6-pin super minimold (Pb-Free) ^{Note} | C3N | Embossed tape 8 mm wide. 1, 2, 3 pins face the perforation side of the tape. Qty 3 kpcs/reel. |

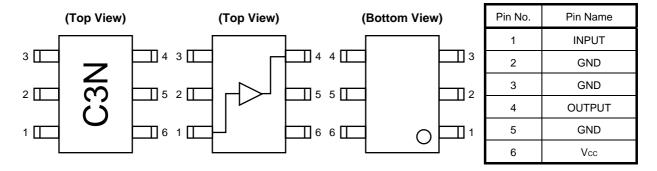
Note With regards to terminal solder (the solder contains lead) plated products (conventionally plated), contact your nearby sales office.

Remark To order evaluation samples, please contact your nearby sales office Part number for sample order: μ PC3226TB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

PIN CONNECTIONS



PRODUCT LINE-UP OF 5 V-BIAS SILICON MMIC MEDIUM OUTPUT POWER AMPLIFIER (TA = $+25^{\circ}$ C, f = 1 GHz, Vcc = Vout = 5.0 V, Zs = ZL = 50 Ω)

| Part No. | fu (GHz) | Po _(sat) (dBm) | G _P (dB) | NF (dB) | lcc (mA) | Package | Marking |
|-----------|-------------|------------------------------|------------------------|---------------------|-------------|----------------------|---------|
| μPC2708TB | 2.9 | +10.0 | 15 | 6.5 | 26 | 6-pin super minimold | C1D |
| μPC2709TB | 2.3 | +11.5 | 23 | 5.0 | 25 | | C1E |
| μPC2710TB | 1.0 | +13.5 | 33 | 3.5 | 22 | | C1F |
| μPC2776TB | 2.7 | +8.5 | 23 | 6.0 | 25 | | C2L |
| μPC3223TB | 3.2 | +12.0 | 23 | 4.5 | 19 | | C3J |
| μPC3225TB | 2.8 | +15.5 ^{Note} | 32.5 Note | 3.7 ^{Note} | 24.5 | | C3M |
| μPC3226TB | 3.2 | +13.0 | 25 | 5.3 | 15.5 | | C3N |

Note μ PC3225TB is f = 0.95 GHz

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

ABSOLUTE MAXIMUM RATINGS

| Parameter | Symbol | Conditions | Ratings | Unit |
|-------------------------------|--------|------------------------------------|-------------|------|
| Supply Voltage | Vcc | T _A = +25°C | 6.0 | V |
| Total Circuit Current | Icc | T _A = +25°C | 40 | mA |
| Power Dissipation | PD | T _A = +85°C Note | 270 | mW |
| Operating Ambient Temperature | TA | | -40 to +85 | °C |
| Storage Temperature | Tstg | | –55 to +150 | °C |
| Input Power | Pin | T _A = +25°C | +10 | dBm |

Note $% 10^{-1}$ Mounted on double-sided copper-clad 50 \times 50 \times 1.6 mm epoxy glass PWB $^{-1}$

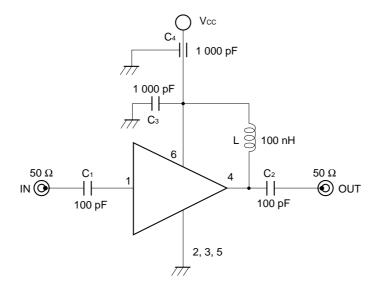
RECOMMENDED OPERATING RANGE

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------------------|--------|------------|------|------|------|------|
| Supply Voltage | Vcc | | 4.5 | 5.0 | 5.5 | V |
| Operating Ambient Temperature | TA | | -40 | +25 | +85 | °C |

ELECTRICAL CHARACTERISTICS (T_A = +25°C, V_{CC} = V_{out} = 5.0 V, Z_S = Z_L = 50 Ω)

| Parameter | Symbol | Test Conditions | MIN. | TYP. | MAX. | Unit |
|---|---------------------|---|-------|-------|------|------|
| Circuit Current | lcc | No input signal | 12.5 | 15.5 | 19.5 | mA |
| Power Gain 1 | G⊳1 | f = 0.1 GHz, P _{in} = -30 dBm | 22.0 | 24.0 | 26.0 | dB |
| Power Gain 2 | G⊳2 | f = 1.0 GHz, P _{in} = -30 dBm | 23.0 | 25.0 | 27.5 | |
| Power Gain 3 | G⊦3 | f = 1.8 GHz, P _{in} = -30 dBm | 23.0 | 26.0 | 29.0 | |
| Power Gain 4 | G⊦4 | f = 2.2 GHz, P _{in} = -30 dBm | 23.0 | 26.0 | 29.0 | |
| Power Gain 5 | G⊳5 | f = 2.6 GHz, P _{in} = -30 dBm | 22.5 | 25.5 | 29.0 | |
| Power Gain 6 | G⊧6 | f = 3.0 GHz, P _{in} = -30 dBm | 22.0 | 25.0 | 28.5 | |
| Saturated Output Power 1 | Po (sat) 1 | f = 1.0 GHz, P _{in} = -2 dBm | +10.0 | +13.0 | l | dBm |
| Saturated Output Power 2 | Po (sat) 2 | f = 2.2 GHz, P _{in} = -8 dBm | +6.0 | +9.0 | - | |
| Gain 1 dB Compression Output Power 1 | Po (1 dB) 1 | f = 1.0 GHz | +5.0 | +7.5 | l | dBm |
| Gain 1 dB Compression Output Power 2 | Po (1 dB) 2 | f = 2.2 GHz | +3.0 | +5.7 | - | |
| Noise Figure 1 | NF1 | f = 1.0 GHz | - | 5.3 | 6.0 | dB |
| Noise Figure 2 | NF2 | f = 2.2 GHz | - | 4.9 | 6.0 | |
| Isolation 1 | ISL1 | f = 1.0 GHz, P _{in} = -30 dBm | 31 | 34 | - | dB |
| Isolation 2 | ISL2 | f = 2.2 GHz, P _{in} = -30 dBm | 33 | 36 | - | |
| Input Return Loss 1 | RLin1 | f = 1.0 GHz, P _{in} = -30 dBm | 10.0 | 14.0 | - | dB |
| Input Return Loss 2 | RLin2 | f = 2.2 GHz, P _{in} = -30 dBm | 9.0 | 13.0 | - | |
| Output Return Loss 1 | RL _{out} 1 | f = 1.0 GHz, P _{in} = -30 dBm | 10.0 | 13.0 | - | dB |
| Output Return Loss 2 | RL _{out} 2 | f = 2.2 GHz, P _{in} = -30 dBm | 10.0 | 13.0 | - | |
| Input 3rd Order Distortion Intercept Point 1 | IIP₃1 | f1 = 1 000 MHz, f2 = 1 001 MHz, $P_{in} = -30 \text{ dBm}$ | - | -5.0 | - | dBm |
| Input 3rd Order Distortion Intercept Point 2 | IIP32 | f1 = 2 200 MHz, f2 = 2 201 MHz, P _{in} = -30 dBm | - | -11.0 | - | |
| Output 3rd Order Distortion Intercept Point 1 | OIP ₃ 1 | f1 = 1 000 MHz, f2 = 1 001 MHz, P _{in} = -30 dBm | - | +20.0 | _ | dBm |
| Output 3rd Order Distortion Intercept Point 2 | OIP ₃ 2 | f1 = 2 200 MHz, f2 = 2 201 MHz, P _{in} = -30 dBm | - | +15.0 | _ | |
| 2nd Order Intermodulation Distortion | IM ₂ | f1 = 1 000 MHz, f2 = 1 001 MHz, P _{in} = -30 dBm | - | 43.0 | - | dBc |
| K factor 1 | K1 | f = 1.0 GHz | _ | 1.4 | I | _ |
| K factor 2 | K2 | f = 2.2 GHz | - | 1.6 | - | - |

TEST CIRCUIT



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

| | Туре | Value |
|--------|------------------------|----------|
| C1, C2 | Chip Capacitor | 100 pF |
| C3 | Chip Capacitor | 1 000 pF |
| C4 | Feed-through Capacitor | 1 000 pF |
| L | Chip Inductor | 100 nH |

INDUCTOR FOR THE OUTPUT PIN

The internal output transistor of this IC, to output medium power. To supply current for output transistor, connect an inductor between the Vcc pin (pin 6) and output pin (pin 4). Select inductance, as the value listed above.

The inductor has both DC and AC effects. In terms of DC, the inductor biases the output transistor with minimum voltage drop to output enable high level. In terms of AC, the inductor makes output-port impedance higher to get enough gain. In this case, large inductance and Q is suitable.

CAPACITORS FOR THE Vcc, INPUT AND OUTPUT PINS

Capacitors of 1 000 pF are recommendable as the bypass capacitor for the Vcc pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the Vcc pin is used to minimize ground impedance of Vcc pin. So, stable bias can be supplied against Vcc fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitances are therefore selected as lower impedance against a 50 Ω load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

To obtain a flat gain from 100 MHz upwards, 1 000 pF capacitors are used in the test circuit. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 10 000 pF. Because the coupling capacitors are determined by equation, $C = 1/(2 \pi R fc)$.

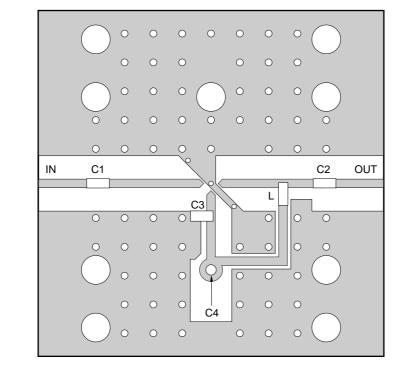


ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

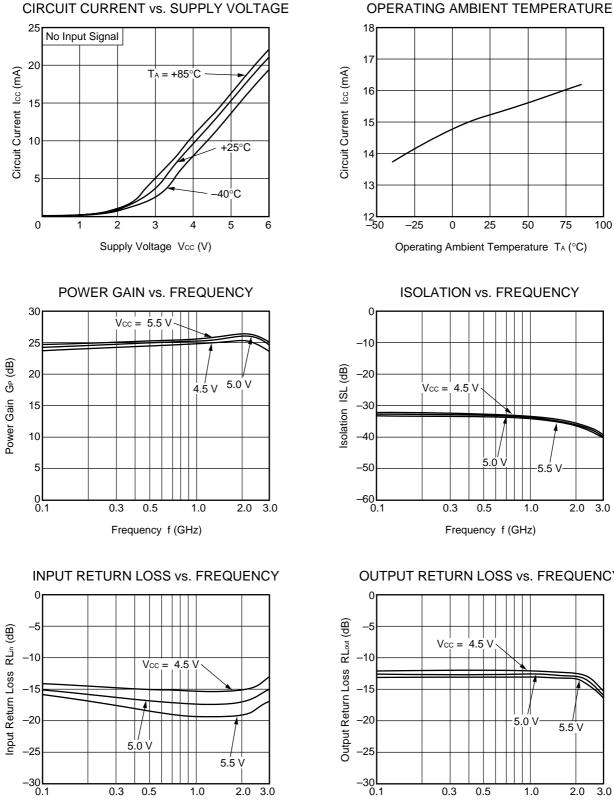
COMPONENT LIST

| | Value |
|--------|----------|
| C1, C2 | 100 pF |
| C3, C4 | 1 000 pF |
| L1 | 100 nH |

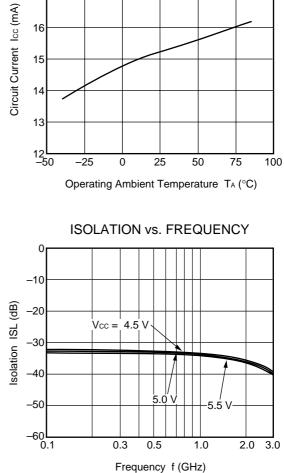
Notes

- 1. $30 \times 30 \times 0.4$ mm double sided copper clad polyimide board.
- 2. Back side: GND pattern
- 3. Solder plated on pattern
- 4. oO: Through holes

TYPICAL CHARACTERISTICS (TA = +25°C, V_{cc} = V_{out} = 5.0 V, Z_s = Z_L = 50 Ω , unless otherwise specified)

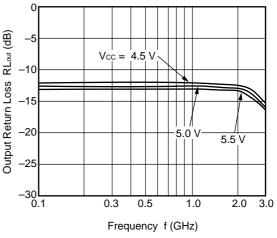


Frequency f (GHz) Remark The graphs indicate nominal characteristics.

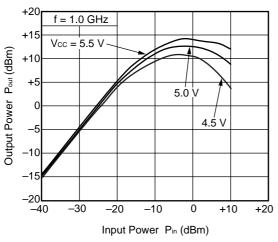


CURCUIT CURRENT vs.

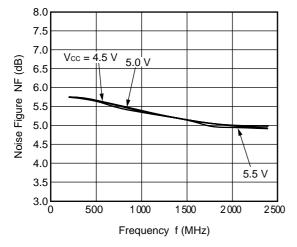
OUTPUT RETURN LOSS vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER

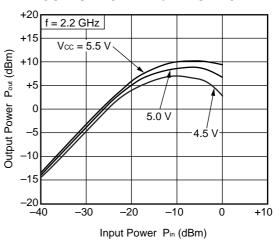


NOISE FIGURE vs. FREQUENCY

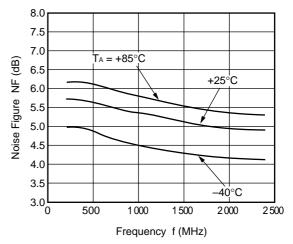


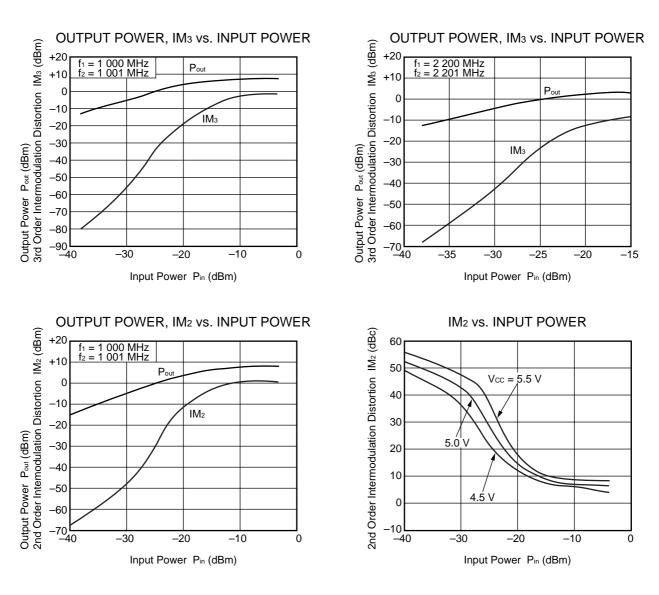
Remark The graphs indicate nominal characteristics.

OUTPUT POWER vs. INPUT POWER



NOISE FIGURE vs. FREQUENCY

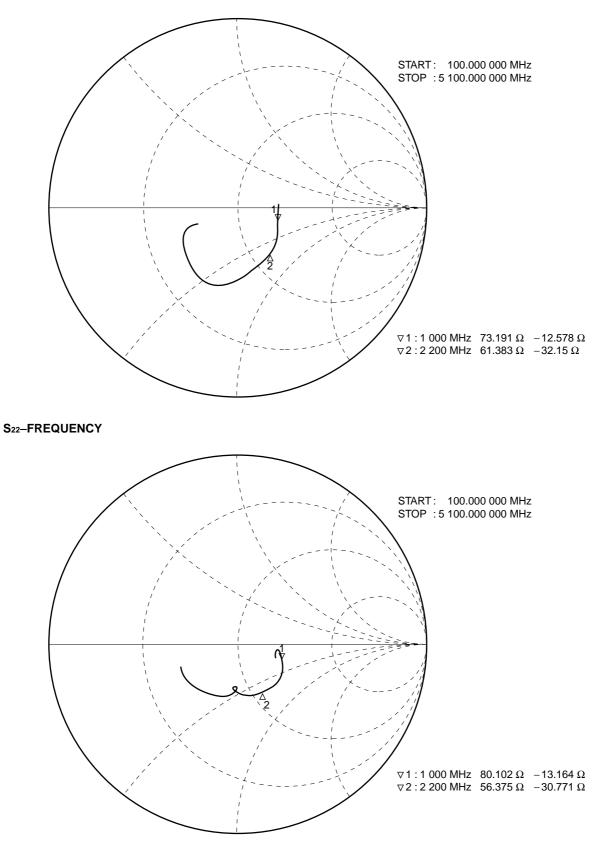




Remark The graphs indicate nominal characteristics.

S-PARAMETERS (TA = +25°C, Vcc = Vout = 5.0 V, Pin = -30 dBm)

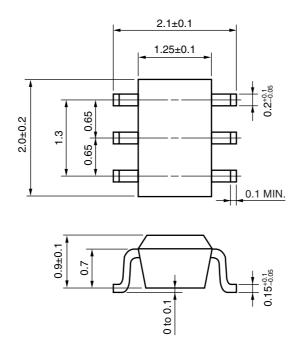
S11-FREQUENCY



Data Sheet PU10558EJ01V0DS

PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)



NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground terminals must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to the Vcc line.
- (4) The inductor (L) must be attached between Vcc and output pins. The inductance value should be determined in accordance with desired frequency.
- (5) The DC cut capacitor must be attached to input and output pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

| Soldering Method | Soldering Conditions | | Condition Symbol |
|------------------|--|---|------------------|
| Infrared Reflow | Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass) | : 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below | IR260 |
| Wave Soldering | Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass) | : 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below | WS260 |
| Partial Heating | Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass) | : 350°C or below : 3 seconds or less : 0.2%(Wt.) or below | HS350 |

Caution Do not use different soldering methods together (except for partial heating).



Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

| Restricted Substance per RoHS | Concentration Limit per RoHS (values are not yet fixed) | Concentration contained in CEL devices | | |
|----------------------------------|--|---|--|--|
| Lead (Pb) | < 1000 PPM | -A -AZ Not Detected (*) | | |
| Mercury | < 1000 PPM | Not Detected | | |
| Cadmium | < 100 PPM | Not Detected | | |
| Hexavalent Chromium | < 1000 PPM | Not Detected | | |
| РВВ | < 1000 PPM | Not Detected | | |
| PBDE | < 1000 PPM | Not Detected | | |

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